

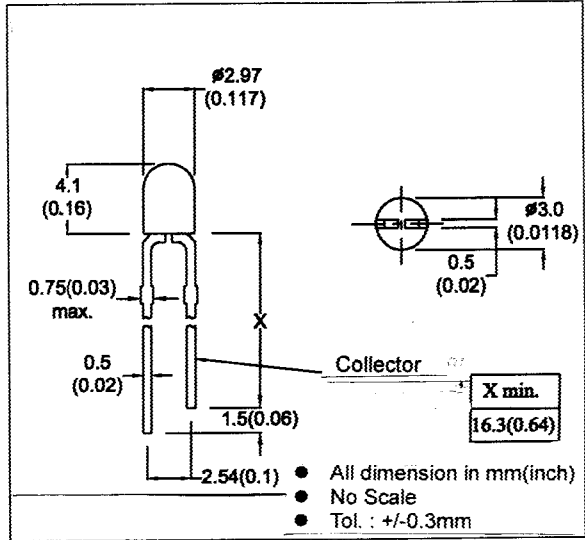
MICRO

PHOTO
DARLINGTON
TRANSISTOR

DESCRIPTION

MDL82 is NPN silicon planar photo darlington transistor. It is encapsulated in a 3mm diameter, low profile and flangeless water clear transparent epoxy package.

It features ultra high illumination sensitivity, fast response time.



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	10V
Emitter-Collector Voltage	V _{ECO}	4V
Continuous Power Dissipation	P _d	50mW
Operating Junction Temperature	T _j	-40 to +85°C
Storage Temperature Range	T _{stg}	-40 to +100°C

ELECTRO-OPTICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	BV _{CEO}	10		V	I _C =100μA E _e =0	
Emitter-Collector Breakdown Voltage	BV _{ECO}	4		V	I _C =100μA E _e =0	
Dark Current	I _D		2000	nA	V _{CE} =10V E _e =0	
Light Current	I _L			mA	V _{CE} =5V E _e =5mW/cm ² *	
		Group A	15			80
		Group B	30			150
		Group C	60			300
Rise Time	T _r	40	TYP	μs	V _{CC} =5V I _C =10mA R _L =100ohm	
Fall Time	T _f	60	TYP	μs	V _{CC} =5V I _C =10mA R _L =100ohm	

* Measured at noted irradiance as emitted from tungsten filament lamp at a color temperature of 2854°K.



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MDL82 TYPICAL CHARACTERISTICS

